O I P E
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PATENT & TRADEMARK OFFICE
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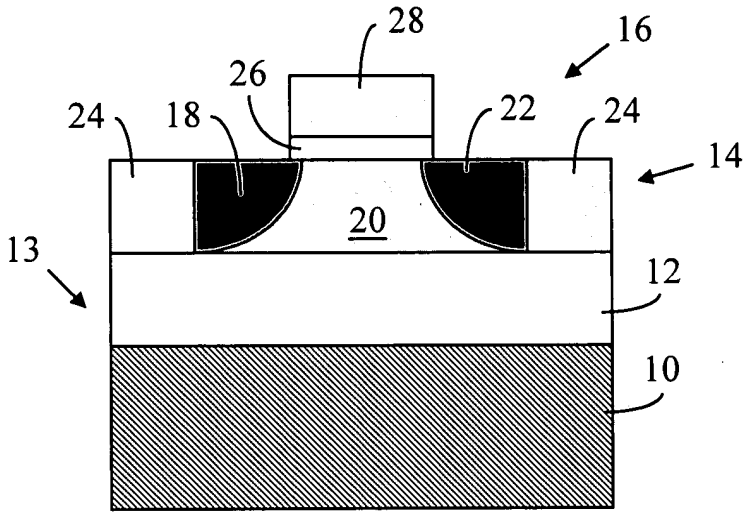

Fig. 1

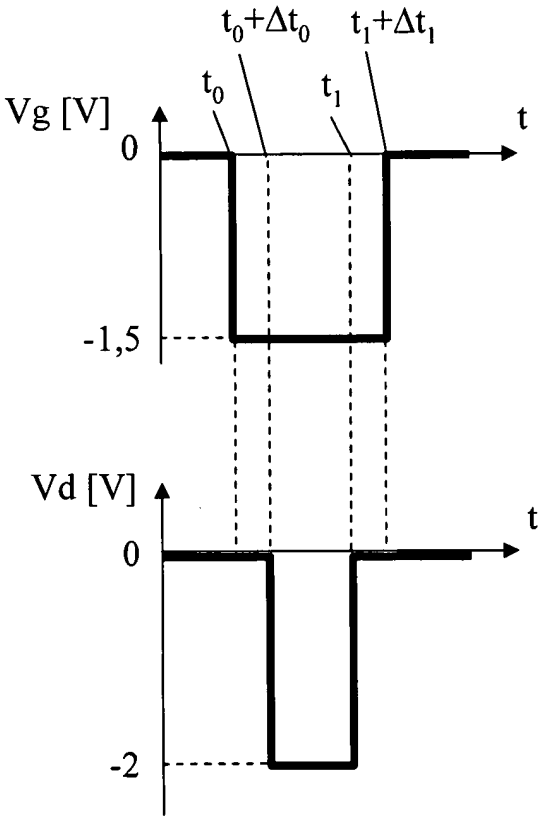

Fig. 2

Fig. 5b

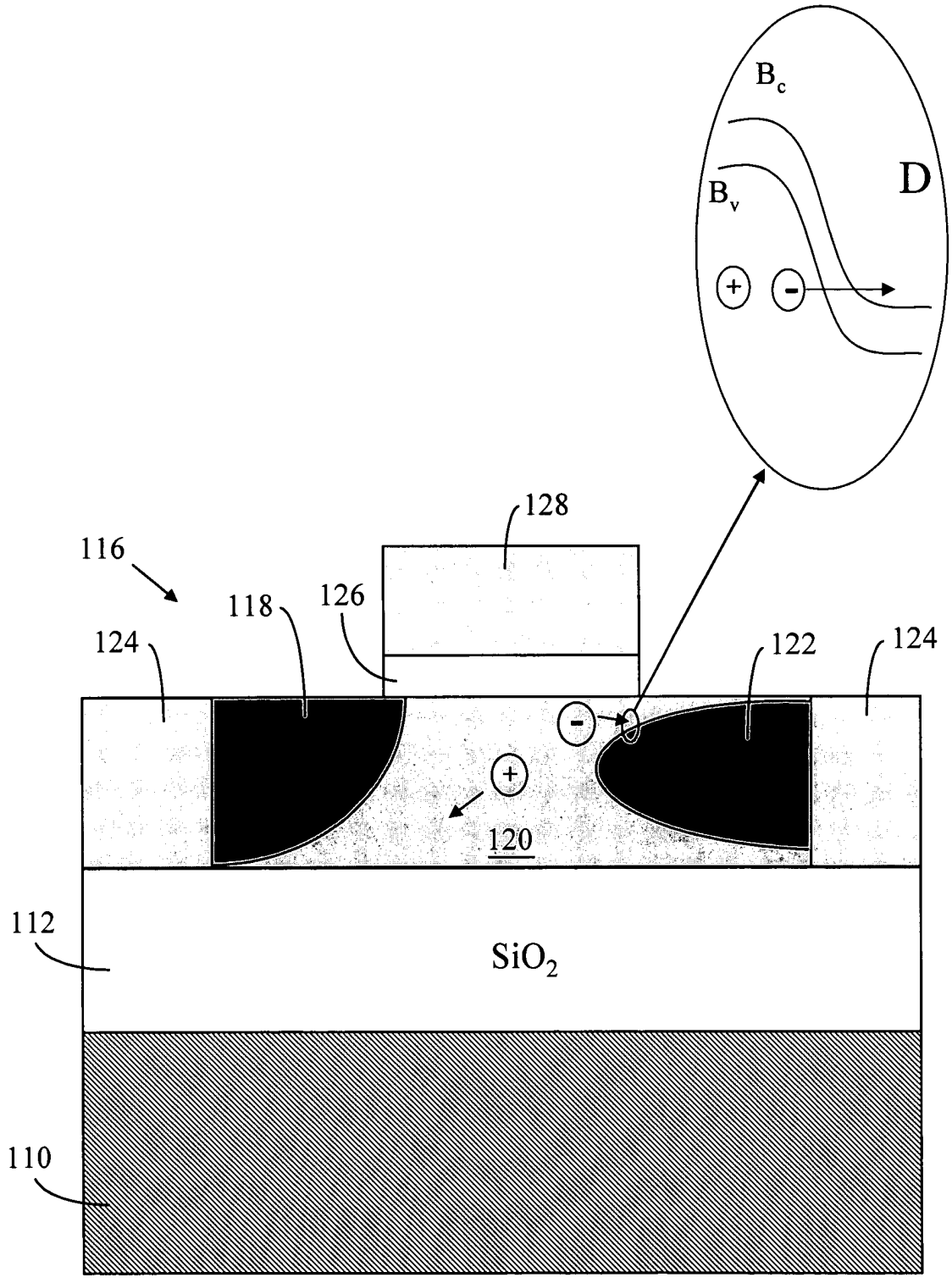

Fig. 5a

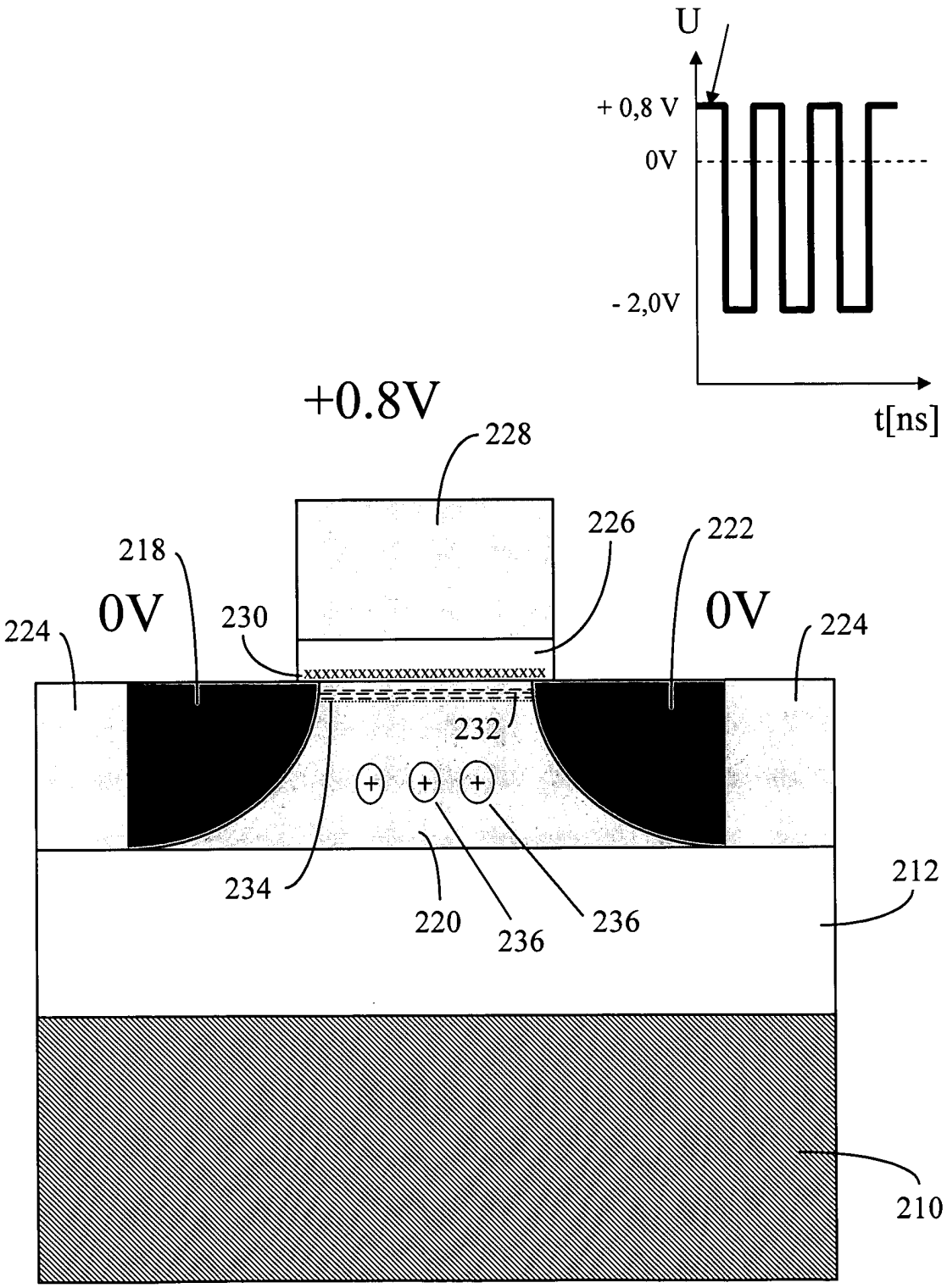
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Fig. 6a

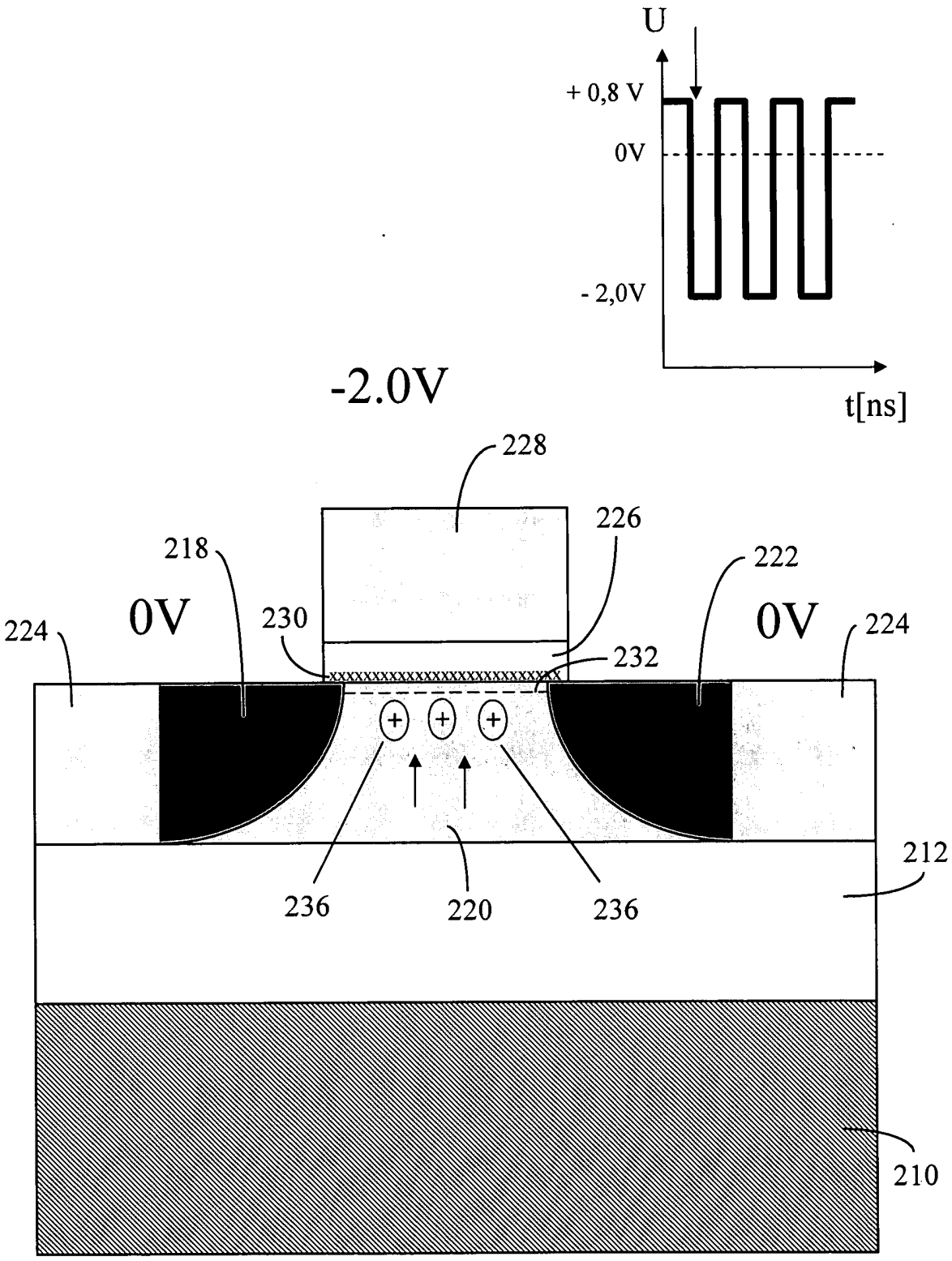
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Fig. 6b

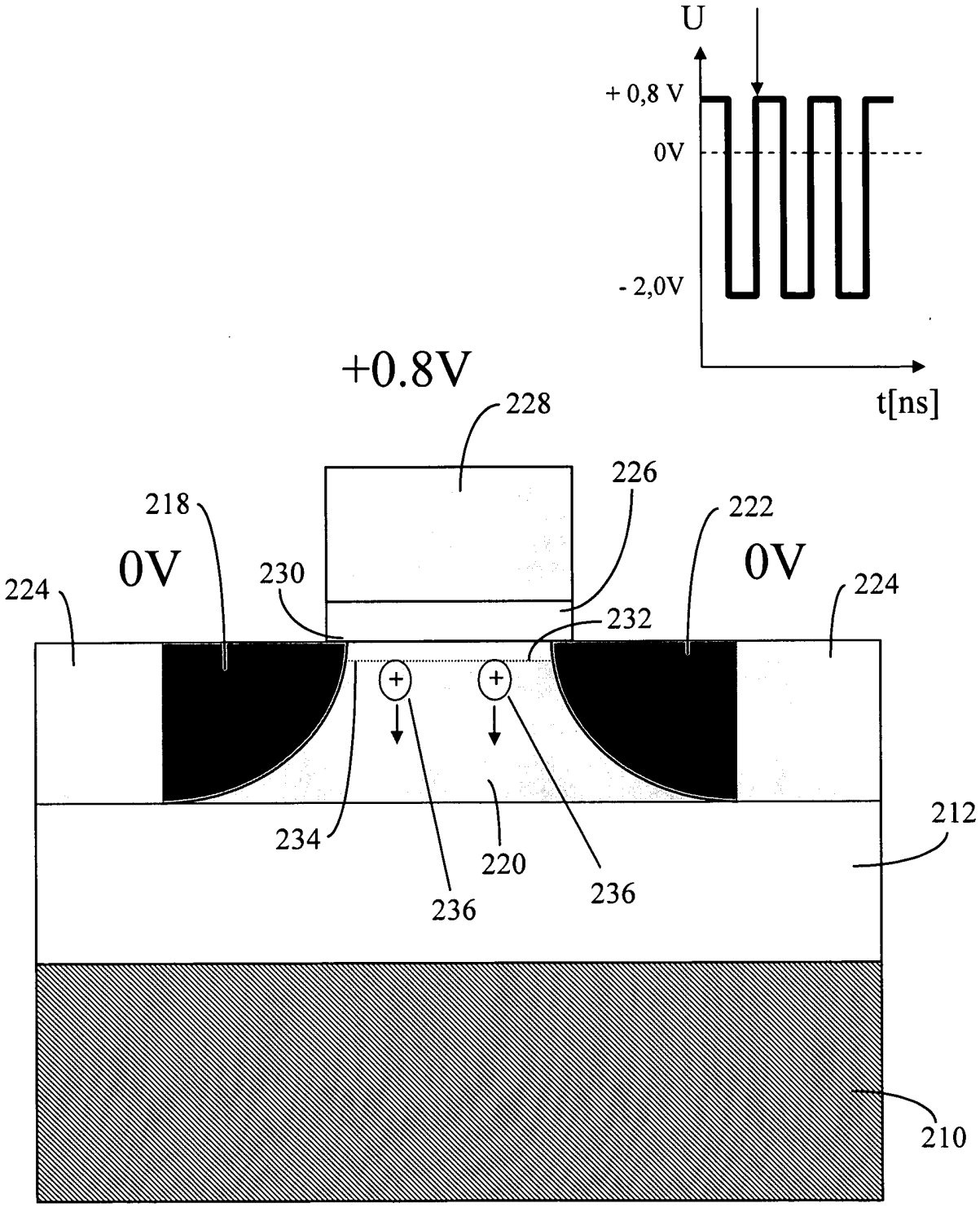
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Fig. 6c

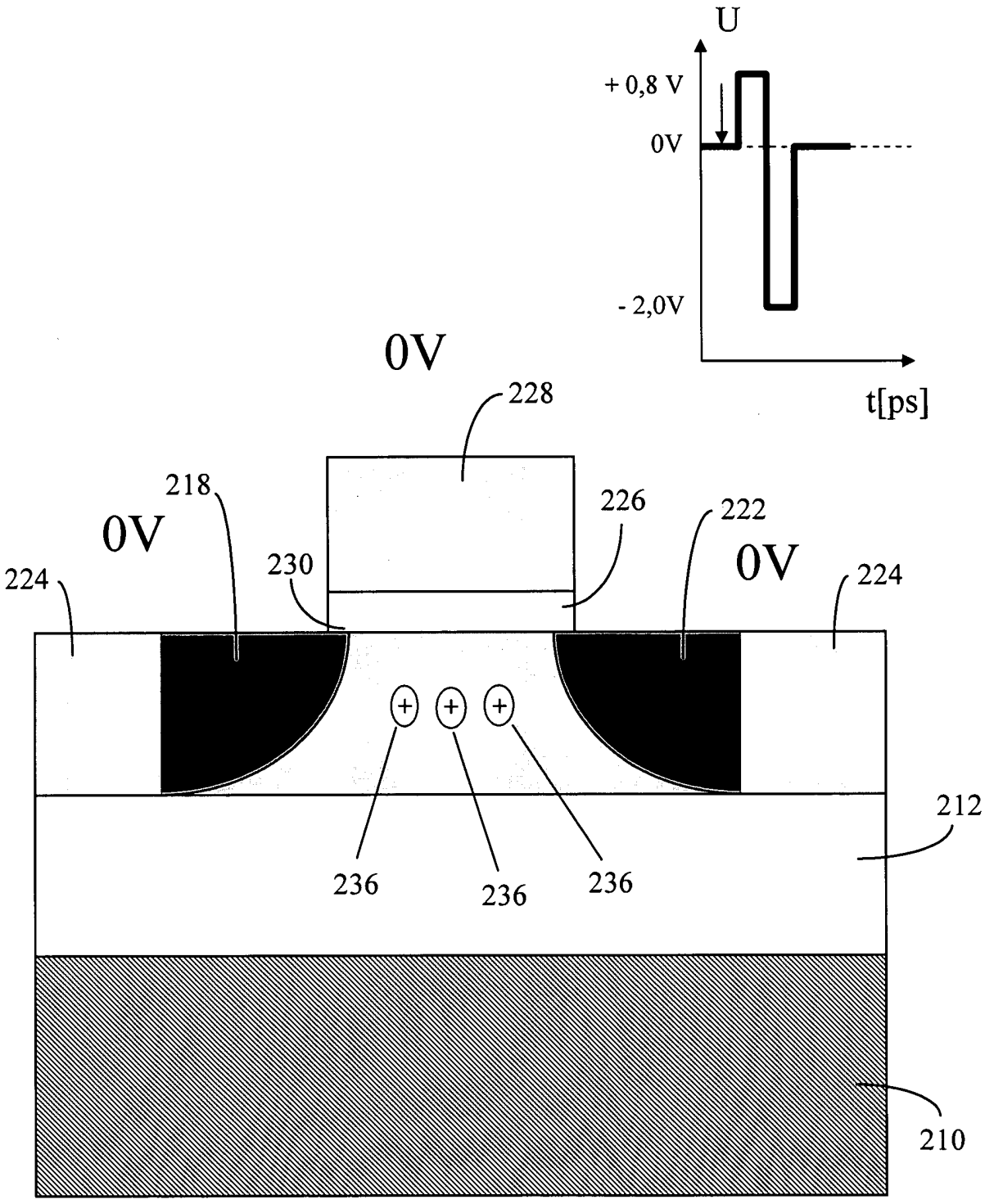
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Fig. 7a

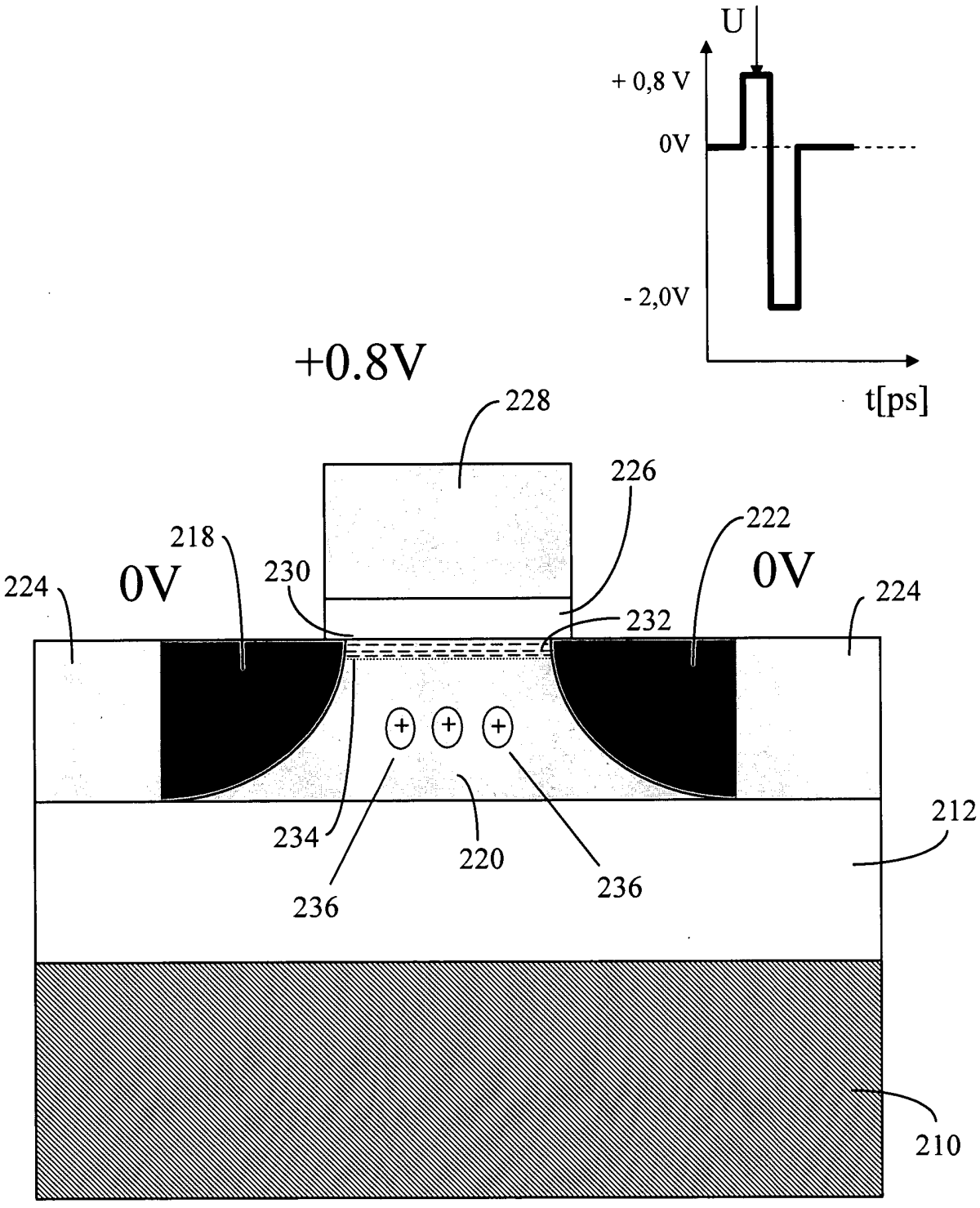
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Fig. 7b

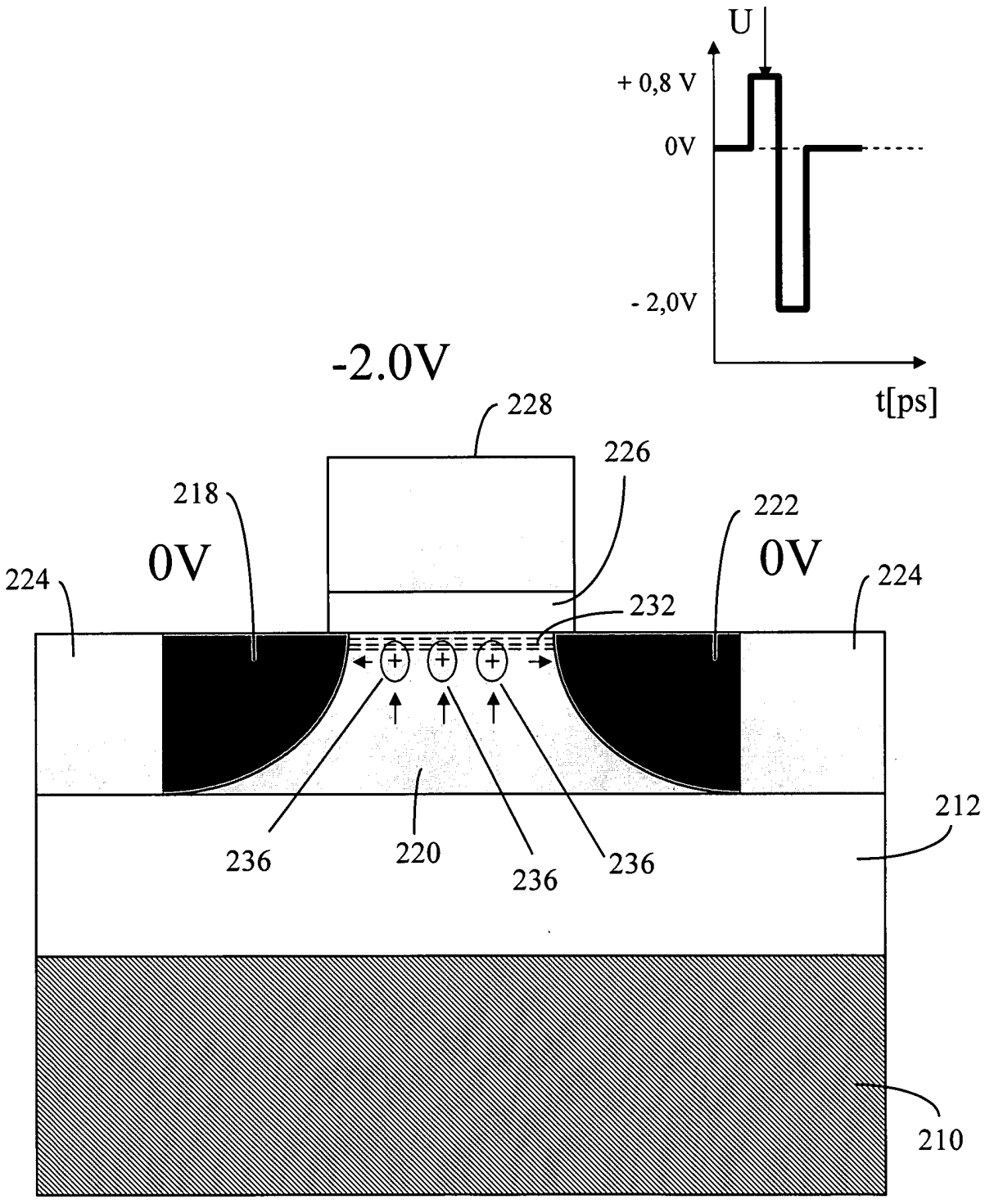
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Fig. 7c

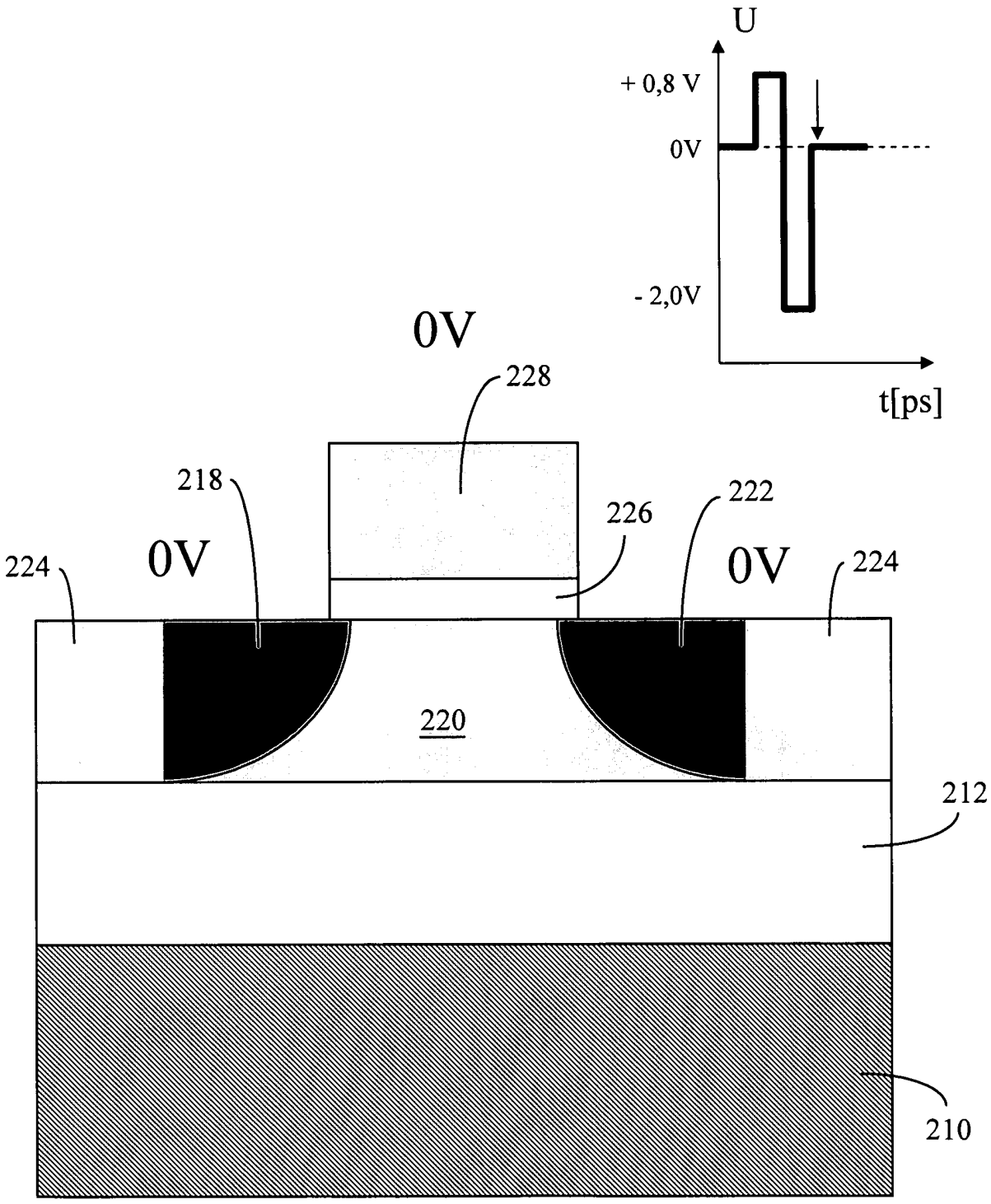

Fig. 7d

PD-SOI
NMOS

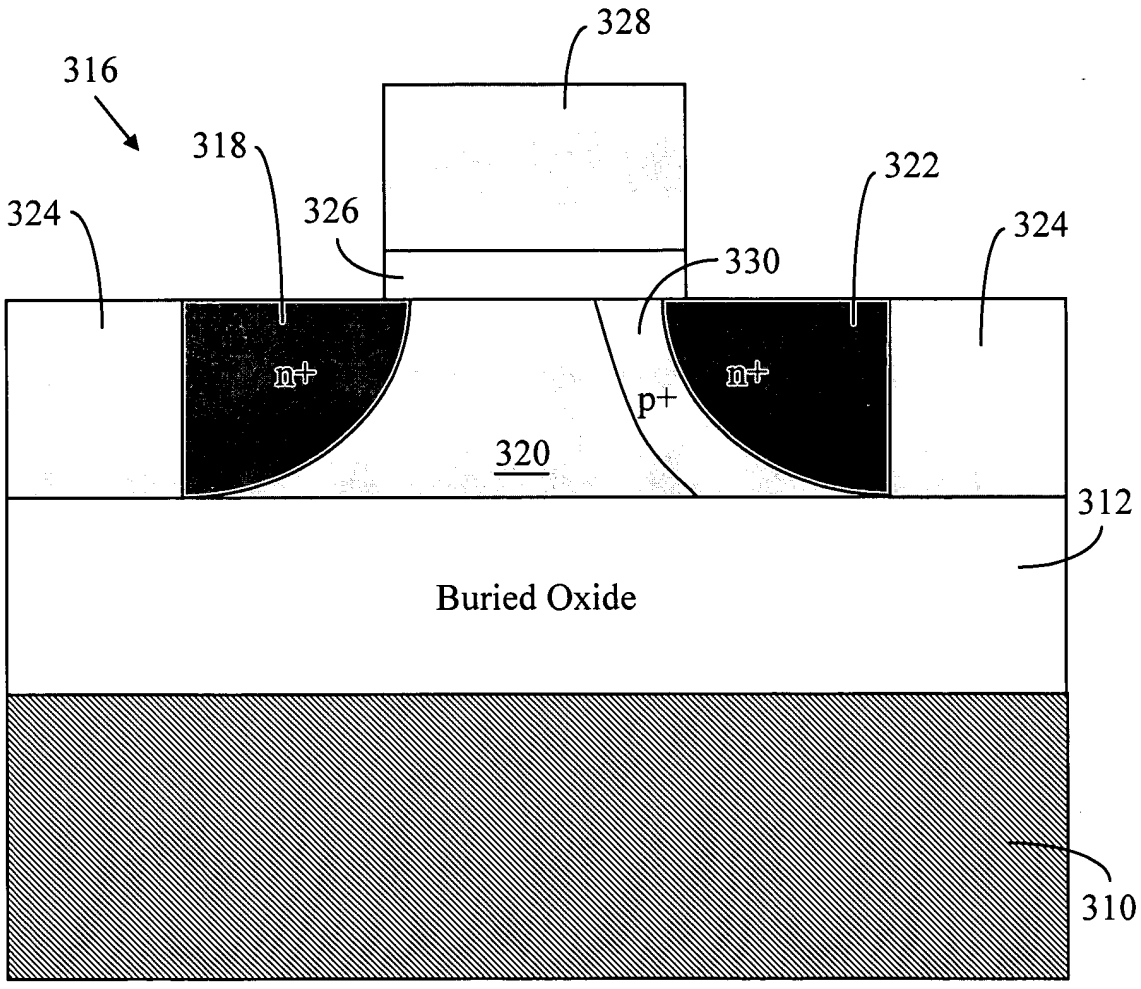

Fig. 8

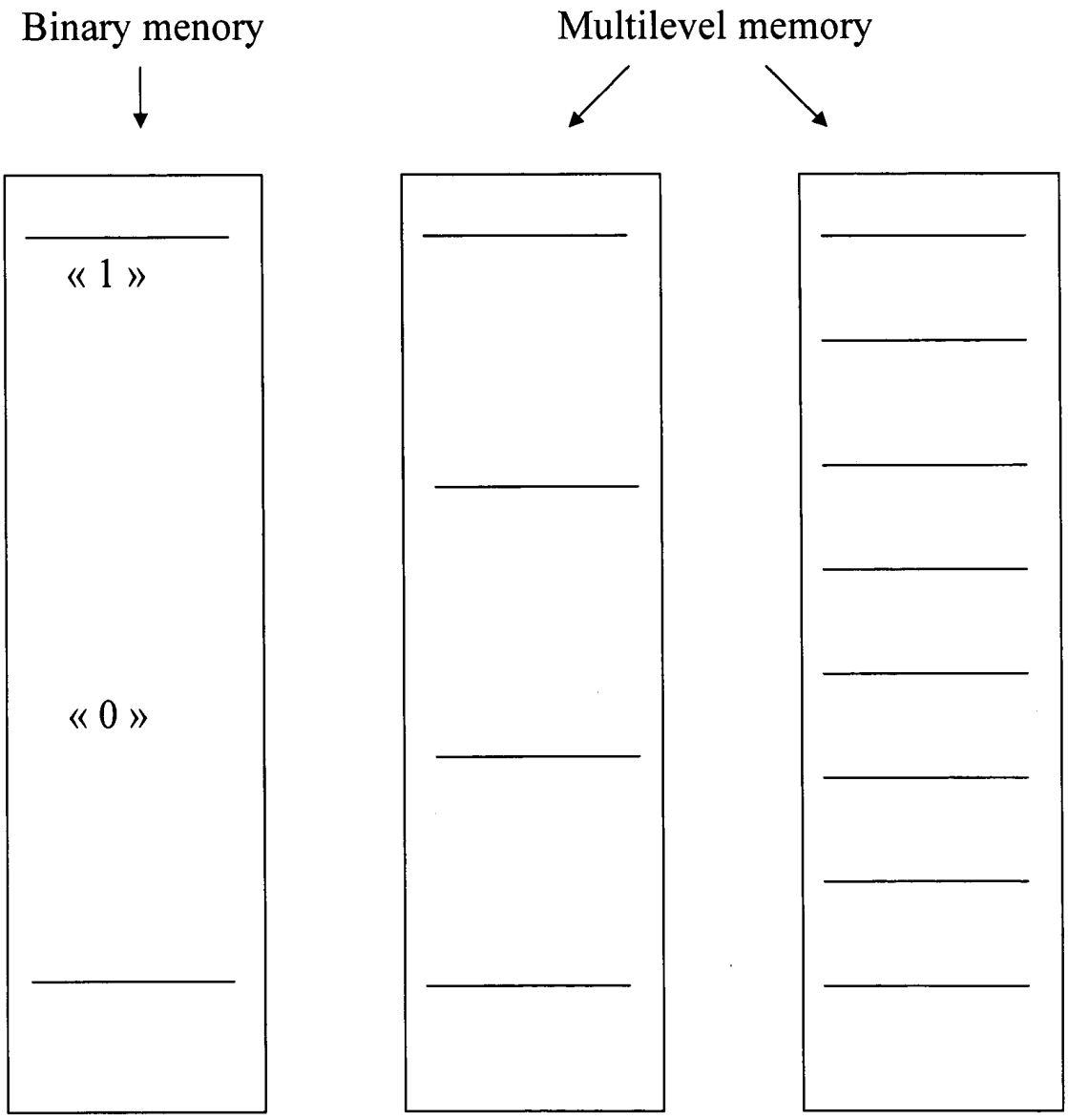

Fig. 10a Fig. 10b Fig. 10c

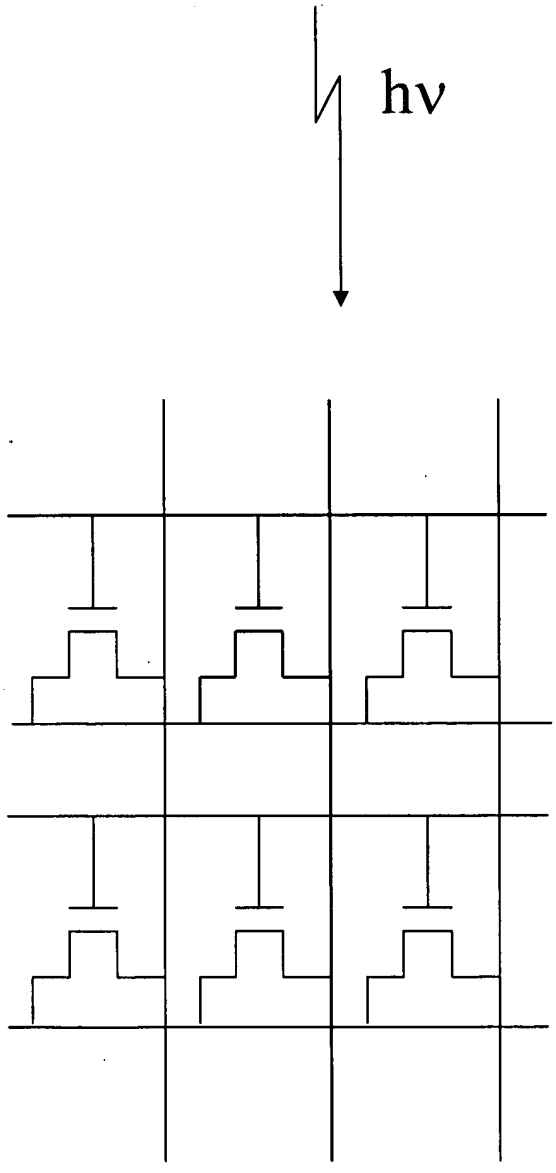

Fig. 18